

SANYO	No.3768A	2SJ195
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

Absolute Maximum Ratings at Ta = 25°C

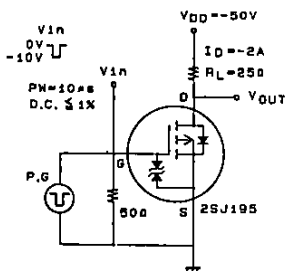
Drain to Source Voltage	V_{DSS}	-100	V	unit
Gate to Source Voltage	V_{GSS}	±15	V	
Drain Current(DC)	I_D	-4	A	
Drain Current(Pulse)	I_{DP}	-16	A	
Allowable Power Dissipation	P_D	30	W	
Channel Temperature	T_{ch}	150	°C	
Storage Temperature	T_{stg}	-55 to +150	°C	

$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$
 $T_c = 25^\circ C$

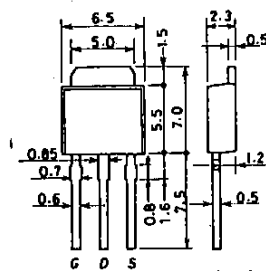
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-100			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	±15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100V, V_{GS} = 0$			-100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -2A$	2.5	4		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -2A, V_{GS} = -10V$		0.3	0.4	Ω
	$R_{DS(on)}$	$I_D = -2A, V_{GS} = -4V$		0.4	0.55	Ω
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		950		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		200		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		40		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		15		ns
Rise Time	t_r	∕		25		ns
Turn-OFF Delay Time	$t_{d(off)}$	∕		90		ns
Fall Time	t_f	∕		70		ns
Diode Forward Voltage	V_{SD}	$I_S = -4A, V_{GS} = 0$	-1.0		-1.5	V

Switching Time Test Circuit

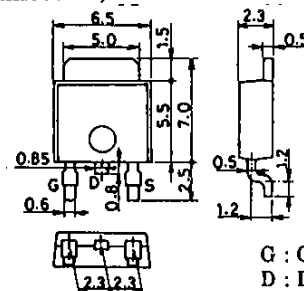


Package Dimensions 2083A (unit : mm)



G : Gate
D : Drain
S : Source
SANYO : TP

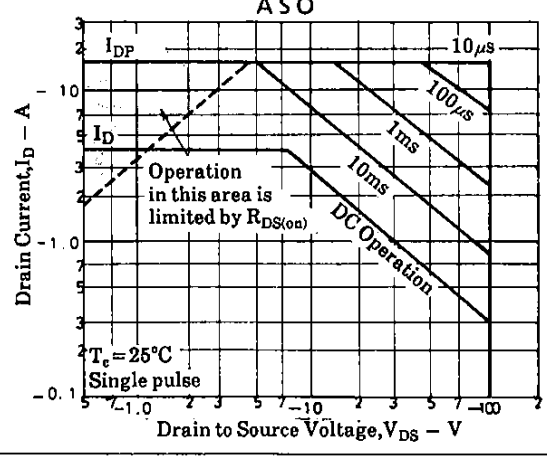
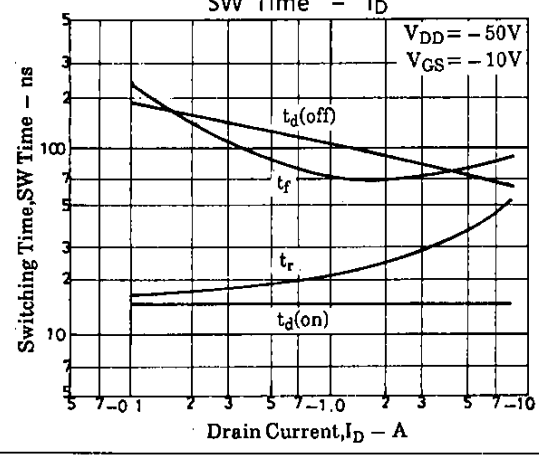
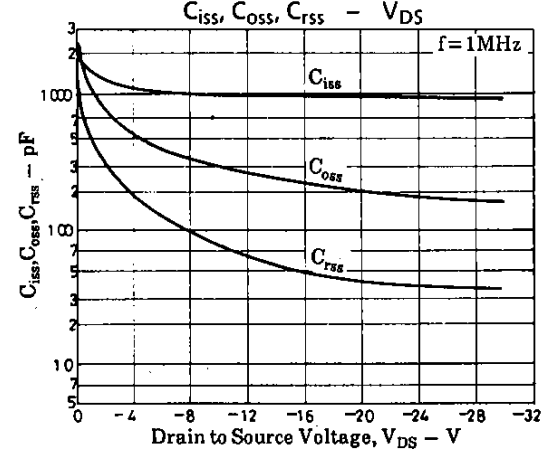
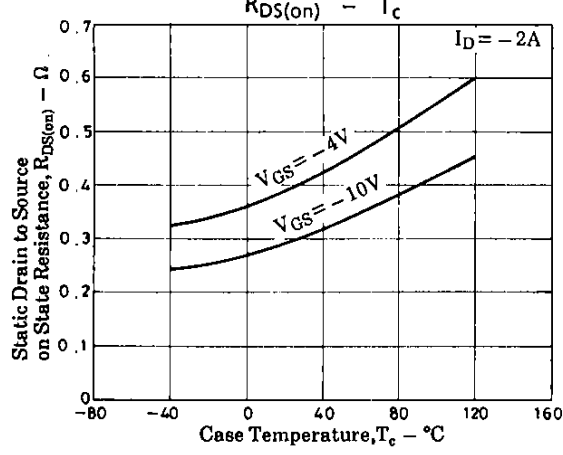
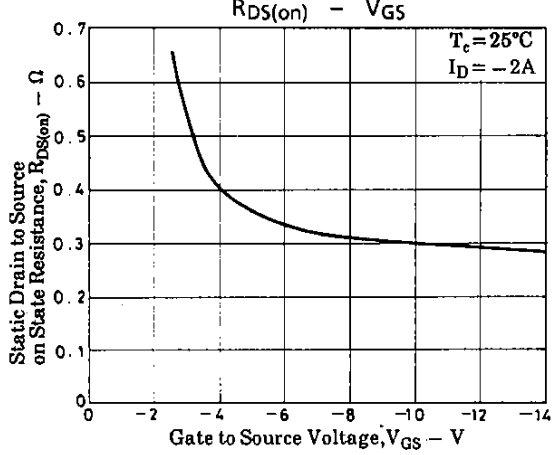
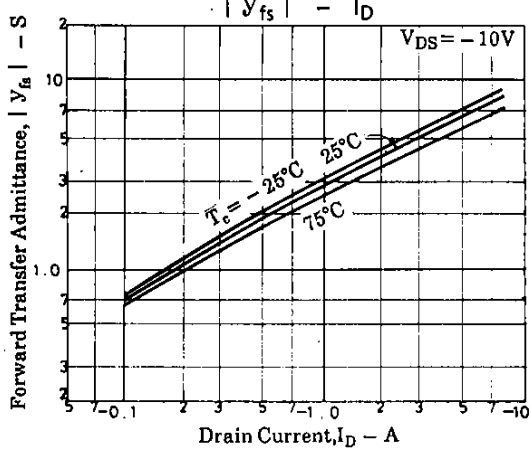
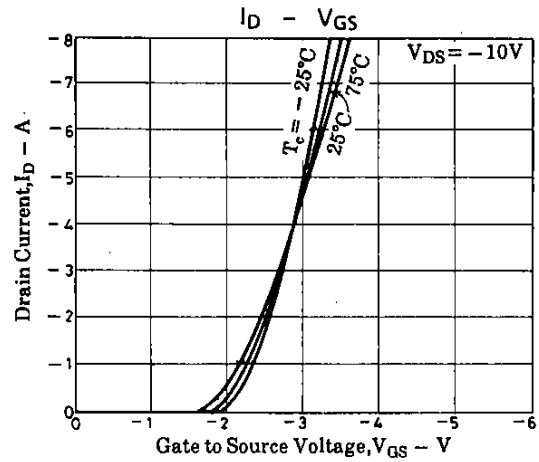
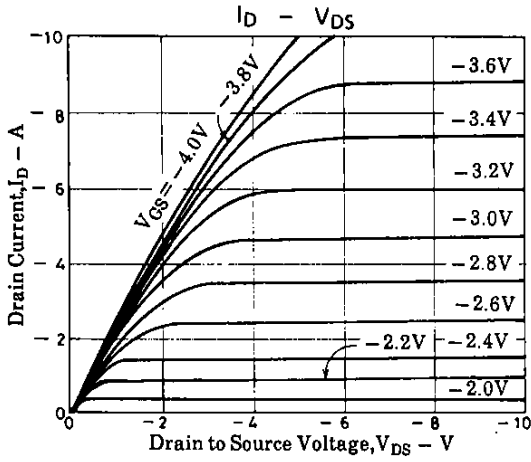
Package Dimensions 2092A (unit : mm)

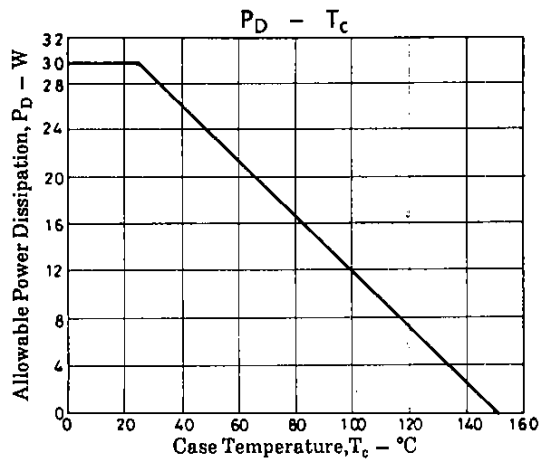


G : Gate
D : Drain
S : Source

SANYO : TP-FA

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